

ABSTRACT OF THE DISCLOSURE

5 A semiconductor device includes a substrate,
a well region formed in the substrate, a field effect
transistor formed in the well region, and a diffused
region, formed across the well region and the substrate
for applying back gate potential to the well region,
and forming a PN junction together with its periphery.
The field effect transistor and the PN junction are
10 connected between terminals for absorbing excess
current so that an internal circuit connected to the
terminals is protected.